

Notice of References Cited	Application/Control No. 10/647,714	Applicant(s)/Patent Under Reexamination KHAN ET AL.	
	Examiner Thao P Le	Art Unit 2818	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,486,502	11-2002	Sheppard et al.	257/194
	B	US-6,246,076	06-2001	Lipkin et al.	257/77
	C	US-			
	D	US-			
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	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	"DC, Microwave, and hng-Temperature Characteristics of GaN FET Structure," S.C. Binari etal., Inst. Phys. Conf. Ser. No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept, 18-22, 1994, pp. 459-462.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.